



# STS4DNF60L

## N-CHANNEL 60V - 0.045 Ω - 4A SO-8 STripFET™ POWER MOSFET

TYPE	V <sub>DSS</sub>	R <sub>DS(on)</sub>	I <sub>D</sub>
STS4DNF60L	60 V	<0.055 Ω	4 A

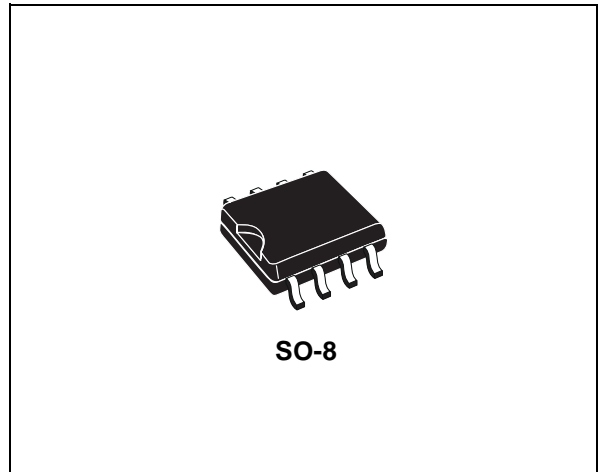
- TYPICAL R<sub>DS(on)</sub> = 0.045 Ω
- STANDARD OUTLINE FOR EASY AUTOMATED SURFACE MOUNT ASSEMBLY
- LOW THRESHOLD DRIVE

### DESCRIPTION

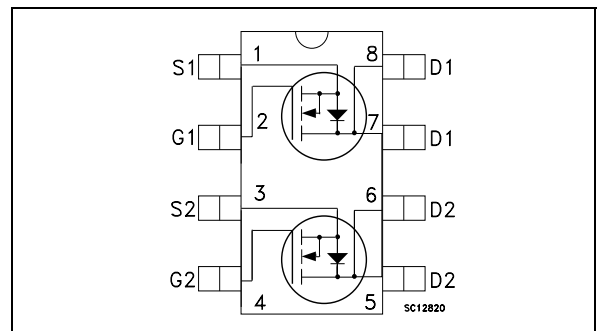
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

### APPLICATIONS

- DC MOTOR DRIVE
- DC-DC CONVERTERS
- BATTERY MANAGEMENT IN NOMADIC EQUIPMENT
- POWER MANAGEMENT IN PORTABLE/DESKTOP PCs



### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>DS</sub>	Drain-source Voltage (V <sub>GS</sub> = 0)	60	V
V <sub>DGR</sub>	Drain-gate Voltage (R <sub>GS</sub> = 20 kΩ)	60	V
V <sub>GS</sub>	Gate- source Voltage	± 15	V
I <sub>D</sub>	Drain Current (continuous) at T <sub>C</sub> = 25°C Single Operation	4	A
	Drain Current (continuous) at T <sub>C</sub> = 100°C Single Operation	2.5	A
I <sub>DM</sub> (●)	Drain Current (pulsed)	16	A
P <sub>tot</sub>	Total Dissipation at T <sub>C</sub> = 25°C Dual Operation	2.5	W
	Total Dissipation at T <sub>C</sub> = 25°C Single Operation	1.6	W

(●) Pulse width limited by safe operating area.

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## THERMAL DATA

Rthj-amb	(*)Thermal Resistance Junction-ambient	Single Operation	78	°C/W
		Dual Operating	62.5	°C/W
T <sub>j</sub>	Thermal Operating Junction-ambient		150	°C
T <sub>stg</sub>	Storage Temperature		-55 to 175	°C

(\*) Mounted on FR-4 board (t ≤ 10 sec.)

## ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25 °C unless otherwise specified)

### OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>(BR)DSS</sub>	Drain-source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0	60			V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current (V <sub>GS</sub> = 0)	V <sub>DS</sub> = Max Rating V <sub>DS</sub> = Max Rating T <sub>C</sub> = 125°C			1 10	μA μA
I <sub>GSS</sub>	Gate-body Leakage Current (V <sub>DS</sub> = 0)	V <sub>GS</sub> = ± 15V			±100	nA

### ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> I <sub>D</sub> = 250 μA	1	1.7	2.5	V
R <sub>DS(on)</sub>	Static Drain-source On Resistance	V <sub>GS</sub> = 10 V I <sub>D</sub> = 2 A V <sub>GS</sub> = 4.5 V I <sub>D</sub> = 2 A		0.045 0.050	0.055 0.065	Ω Ω

### DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g <sub>fs</sub> (*)	Forward Transconductance	V <sub>DS</sub> > I <sub>D(on)</sub> × R <sub>DS(on)</sub> max I <sub>D</sub> = 2 A		7		S
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, f = 1 MHz, V <sub>GS</sub> = 0		1030		pF
C <sub>oss</sub>	Output Capacitance			140		pF
C <sub>rss</sub>	Reverse Transfer Capacitance			40		pF

**ELECTRICAL CHARACTERISTICS** (continued)

**SWITCHING ON**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on Delay Time Rise Time	$V_{DD} = 30\text{ V}$ $I_D = 2.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 4.5\text{ V}$ (Resistive Load, Figure 3)		15 28		ns ns
$Q_g$ $Q_{gs}$ $Q_{gd}$	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD} = 48\text{ V}$ $I_D = 4\text{ A}$ $V_{GS} = 4.5\text{ V}$		15 4 4		nC nC nC

**SWITCHING OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{r(Voff)}$ $t_f$ $t_c$	Turn-off Delay Time Fall Time Cross-over Time	$V_{clamp} = 48\text{ V}$ $I_D = 5\text{ A}$ $R_G = 4.7\ \Omega$ , $V_{GS} = 4.5\text{ V}$ (Inductive Load, Figure 5)		15 20 20	25	ns ns ns

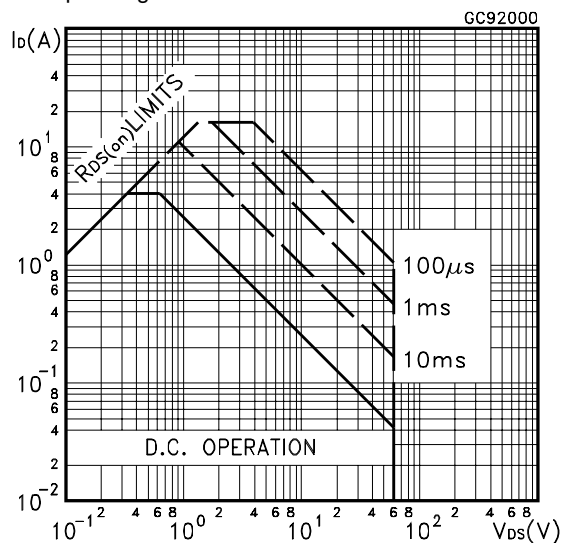
**SOURCE DRAIN DIODE**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM} (\bullet)$	Source-drain Current Source-drain Current (pulsed)				4 16	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 4\text{ A}$ $V_{GS} = 0$			1.2	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 4\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_j = 150^\circ\text{C}$ (see test circuit, Figure 5)		85 85 2		ns nC A

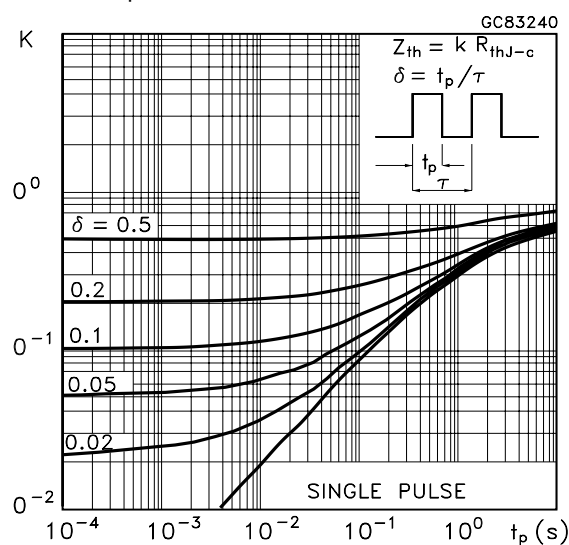
(\*) Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5 %.

( $\bullet$ ) Pulse width limited by safe operating area.

**Safe Operating Area**

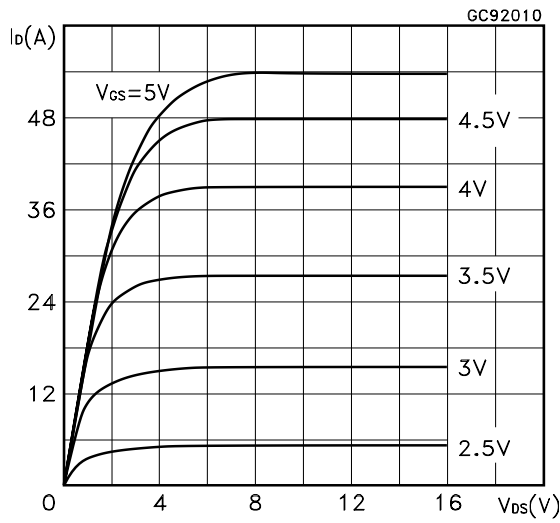


**Thermal Impedance**

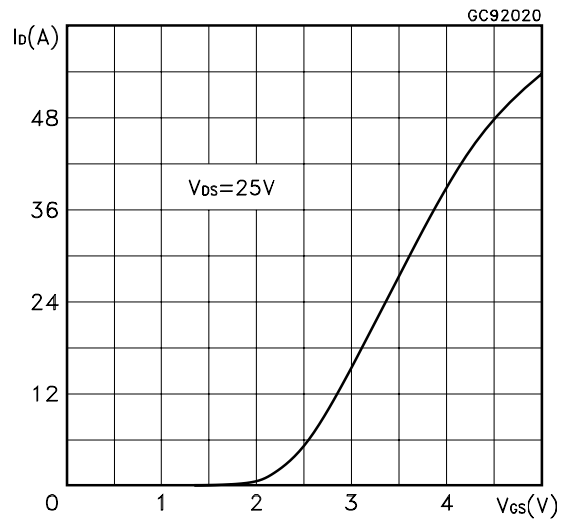


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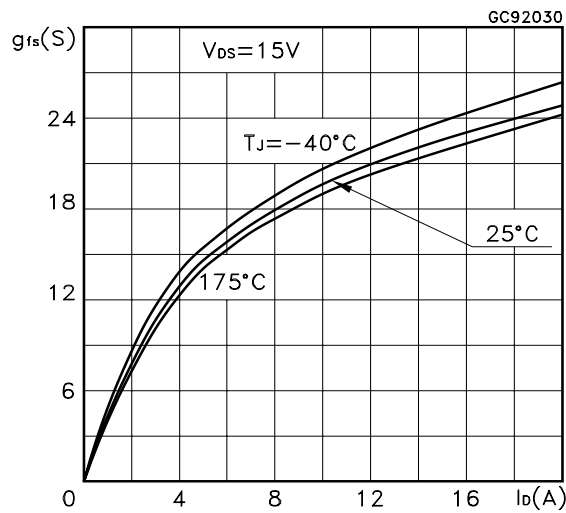
Output Characteristics



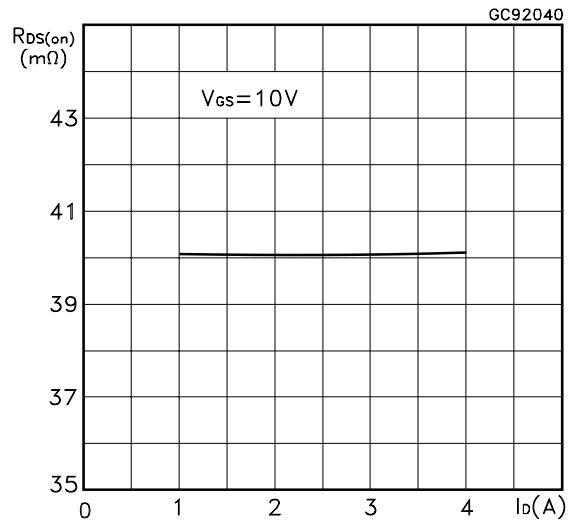
Transfer Characteristics



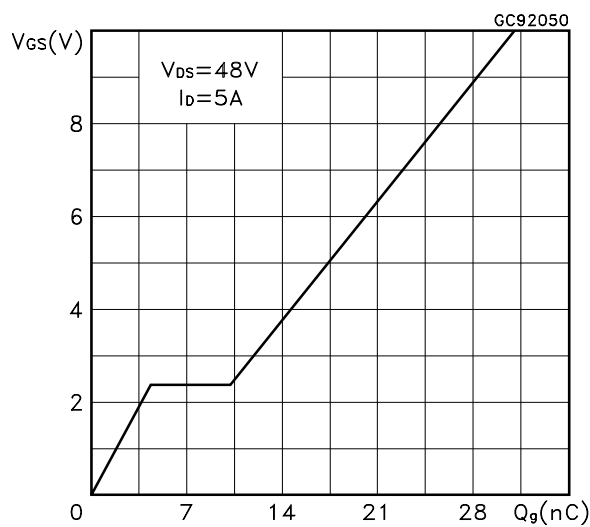
Transconductance



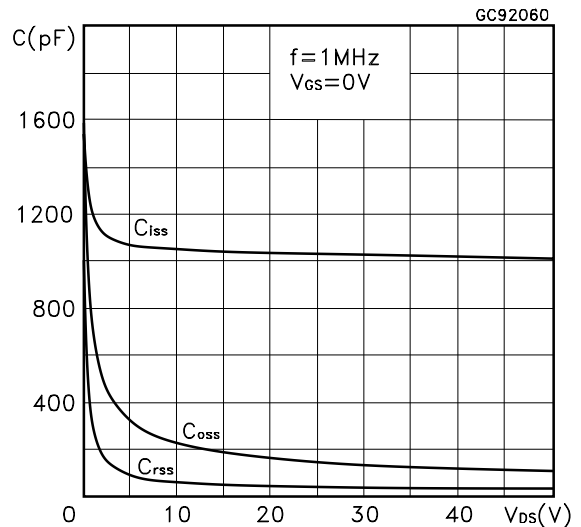
Static Drain-source On Resistance



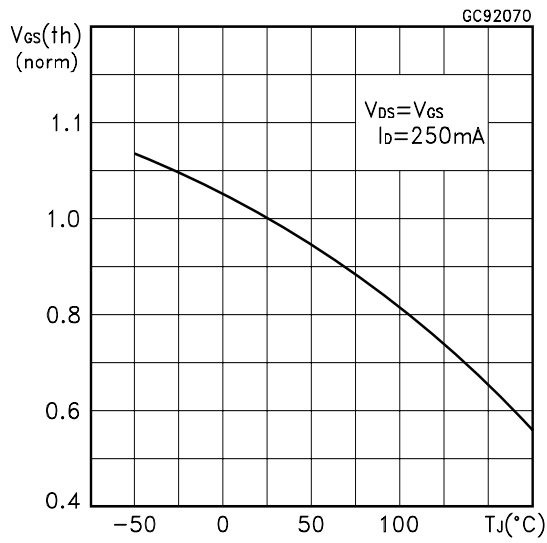
Gate Charge vs Gate-source Voltage



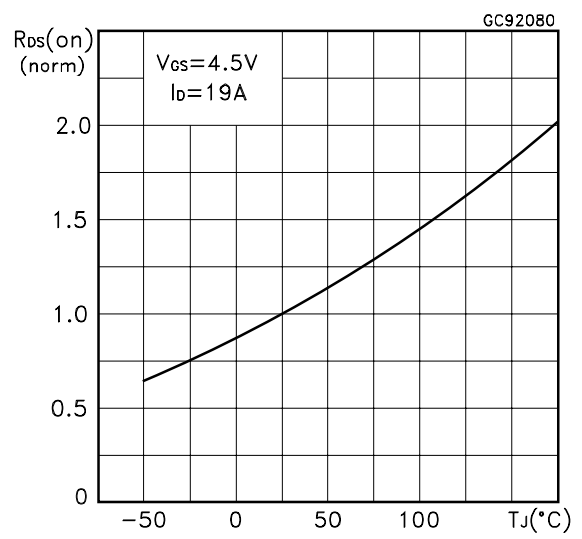
Capacitance Variations



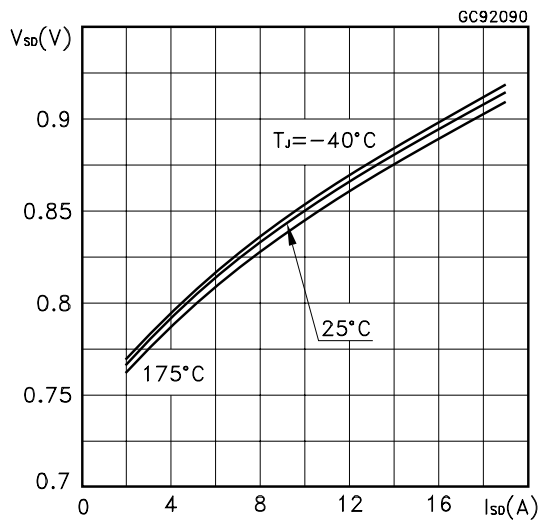
Normalized Gate Threshold Voltage vs Temperature



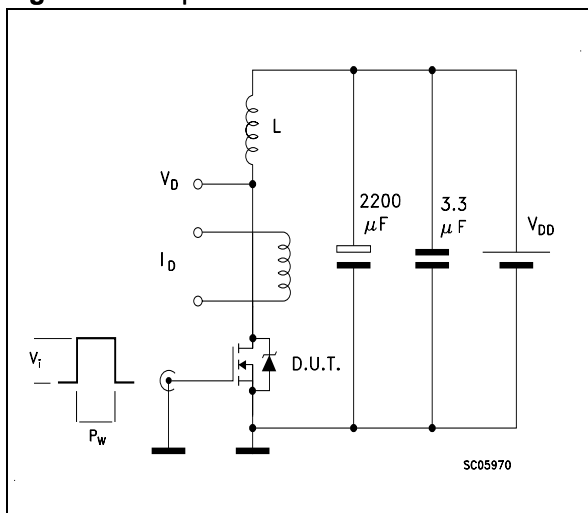
Normalized on Resistance vs Temperature



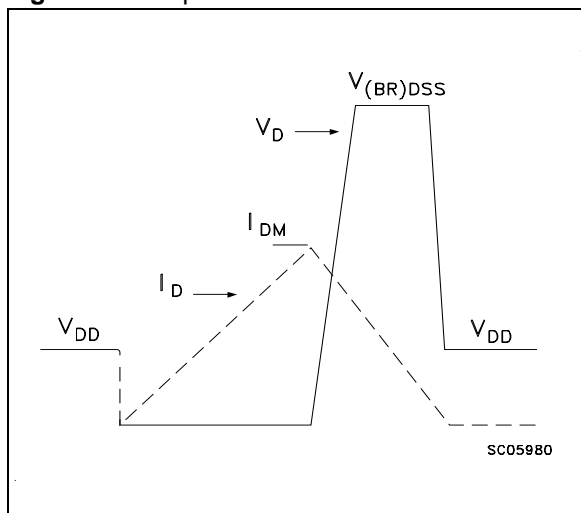
Source-drain Diode Forward Characteristics



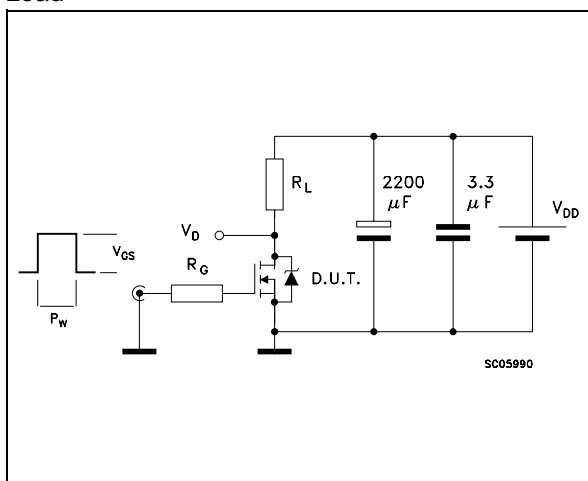
**Fig. 1: Unclamped Inductive Load Test Circuit**



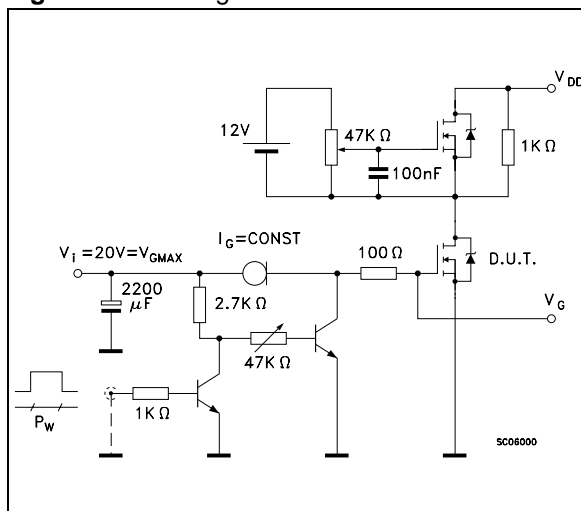
**Fig. 2: Unclamped Inductive Waveform**



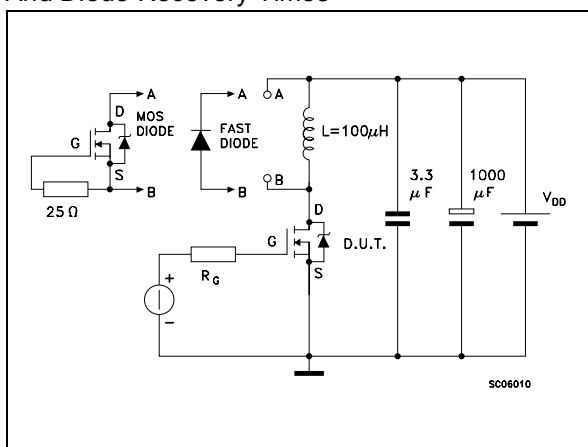
**Fig. 3: Switching Times Test Circuits For Resistive Load**



**Fig. 4: Gate Charge test Circuit**

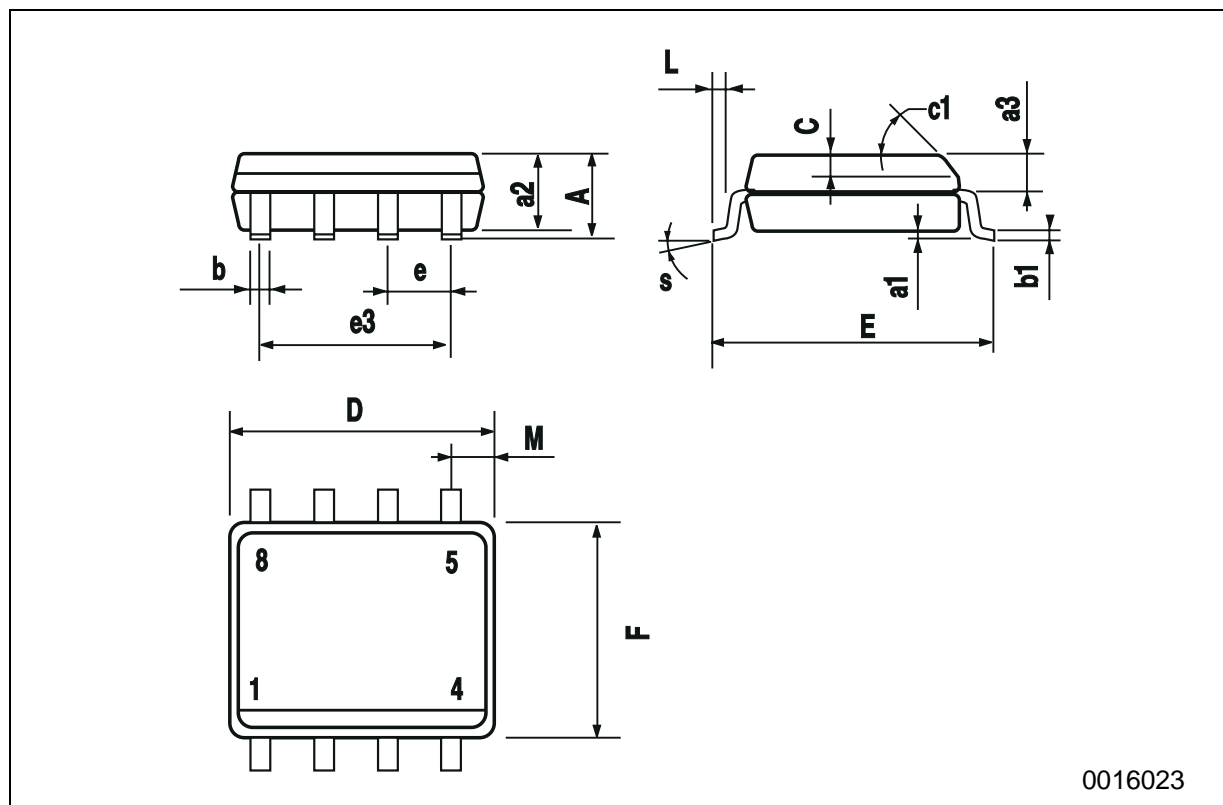


**Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times**



**SO-8 MECHANICAL DATA**

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.25	0.003		0.009
a2			1.65			0.064
a3	0.65		0.85	0.025		0.033
b	0.35		0.48	0.013		0.018
b1	0.19		0.25	0.007		0.010
C	0.25		0.5	0.010		0.019
c1	45 (typ.)					
D	4.8		5.0	0.188		0.196
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.14		0.157
L	0.4		1.27	0.015		0.050
M			0.6			0.023
S	8 (max.)					



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